SGS-THOMSON MICROELECTRONICS

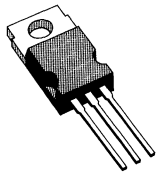
BU406D BU407D/BU408D

HORIZONTAL TV DEFLECTORS

DESCRIPTION

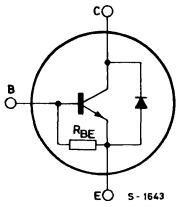
The BU406D, BU407D, and BU408D are silicon planar epitaxial NPN transistors with integrated damper diode, in Jedec TO-220 plastic package. They are fast switching, high voltage devices for use in horizontal deflection output stages of MTV receivers with 110° CRT.

The BU406D and BU408D are primarily intended for large screen, while the BU407D is for medium and small screens.



TO-220

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value			Unit
		BU406D	BU407D	BU408D	
V_{CBO}	Collector-base Voltage (I_E = 0)	400	330	400	V
V_{CEV}	Collector-emitter Voltage (V_{BE} = – 1.5V)	400	330	400	V
V_{EBO}	Emitter-base Voltage (I_C = 0)	6			V
I_C	Collector Current	7			A
I_{CM}	Collector Peak Current (repetitive)	10			A
I_{CM}	Collector Peak Current (t_p = 10ms)	15			A
I_B	Base Current	4			A
P_{tot}	Total Power Dissipation at $T_{case} \leq 25°C$	60			W
T_{stg}	Storage Temperature	– 65 to 150			°C
T_j	Junction Temperature	150			°C

THERMAL DATA

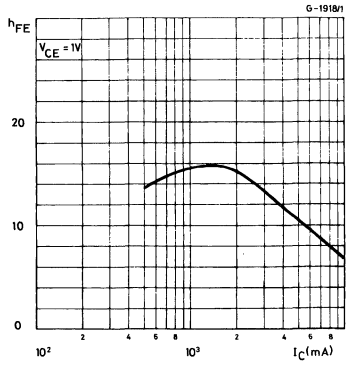
$R_{th\ j\text{-}case}$	Thermal Resistance Junction-case	Max	2.08	°C/W
$R_{th\ j\text{-}amb}$	Thermal Resistance Junction-ambient	Max	70	°C/W

ELECTRICAL CHARACTERISTICS (T_{case} = 25°C unless otherwise specified)

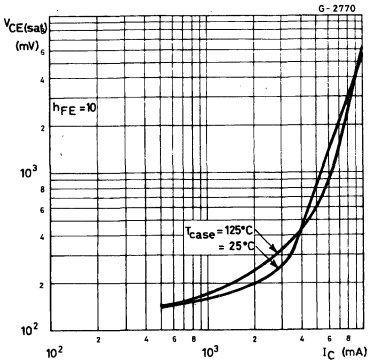
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CEV}	Collector Cutoff Current (V_{BE} = – 1.5V)	for **BU406D** and **BU408D** V_{CE} = 400V for **BU407D** V_{CE} = 330V			15 15	mA mA
I_{EBO}	Emitter Cutoff Current (I_C = 0)	V_{EB} = 6V			400	mA
$V_{CE(sat)}$*	Collector-emitter Saturation Voltage	for **BU406D** and **BU407D** I_C = 5A I_B = 0.65A for **BU408D** I_C = 6A I_B = 1.2A			1 1	V V
$V_{BE(sat)}$*	Base-emitter Saturation Voltage	for **BU406D** and **BU407D** I_C = 5A I_B = 0.65A for **BU408D** I_C = 6A I_B = 1.2A			1.3 1.5	V V
f_T	Transition Frequency	I_C = 0.5A V_{CE} = 10V	10			MHz
t_{off}	Turn-off Time	for **BU406D** and **BU407D** I_C = 5A I_{Bend} = 0.65A for **BU408D** I_C = 6A I_{Bend} = 1.2A			0.75 0.5	µs µs
$I_{s/b}$	Second Breakdown Collector Current	V_{CE} = 40V t = 10ms		4		A
V_F	Diode Forward Voltage	I_F = 5A			1.5	V

* Pulsed : pulse duration = 300µs, duty cycle = 1.5%.

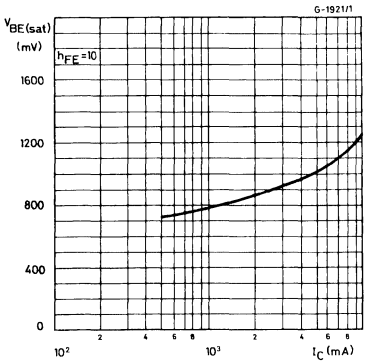
DC Current Gain.



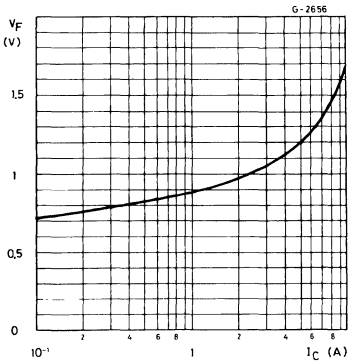
Collector-emitter Saturation Voltage.



Base-emitter Saturation Voltage.

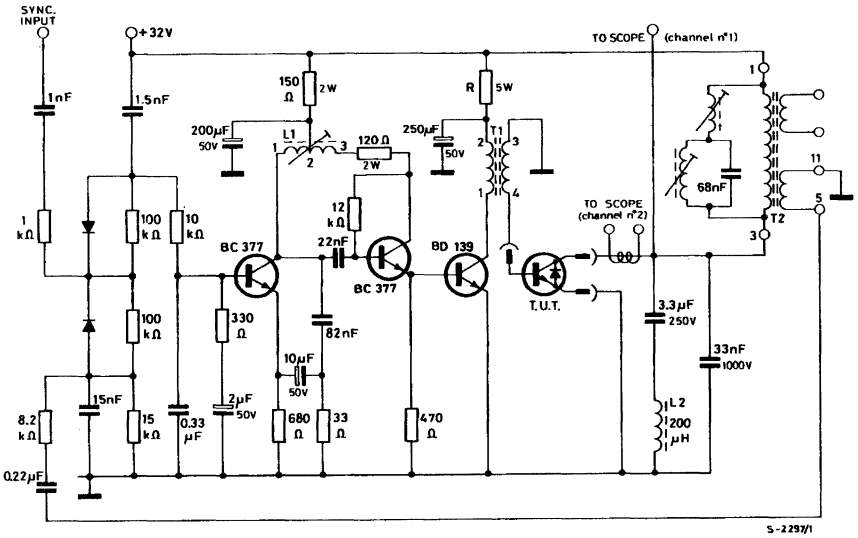


Forward Voltage.



SWITCHING TIMES

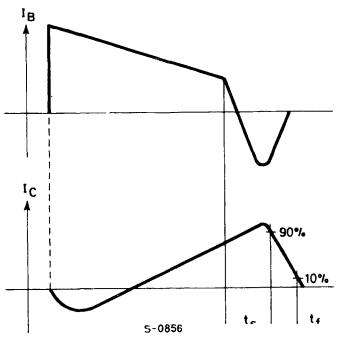
TEST CIRCUIT (FALL, STORAGE AND TURN-OFF TIME)



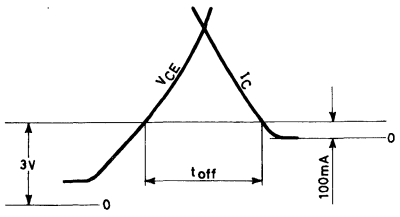
L1 Horizontal hold coil : Pins 1–2 = 75 turns Ø 0.2mm ; R = 1.5Ω ; L min = 0.62mH
Core = siferrit B 62120 25x4x2
Pins 2–3 = 293 turns Ø 0.2mm ; R = 4.8Ω ; L max = 4.1mH
L2 Horizontal yoke = 200µH
T1 Driver transformer : Pins 1–2 = 125 turns Ø 0.2mm ;
Gap = 0.12mm ; Core = 3E3 double E 19x15x5
Pins 3–4 = 25 turns Ø 0.4mm ;
T2 EHT transformer manufacturer ARCO type 249.065/035

R = 270Ω for BU406D and BU407D
R = 180Ω for BU408D

Waveforms



Fall and storage time



Turn-off time is the time for the collector current I_C to decrease to 100mA after the collector to emitter voltage V_{CE} has risen 3V into its flyback excursion

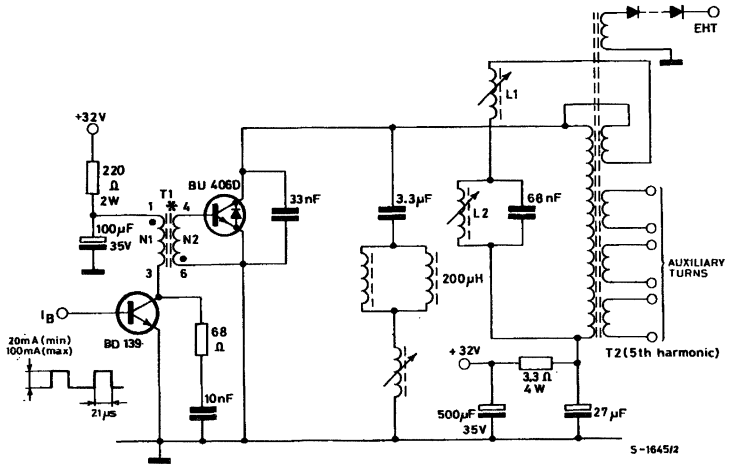
S-0857

Turn-off time

APPLICATION INFORMATION

Two examples are given of the BU406D and BU407D in conventional MTV horizontal deflection circuits.

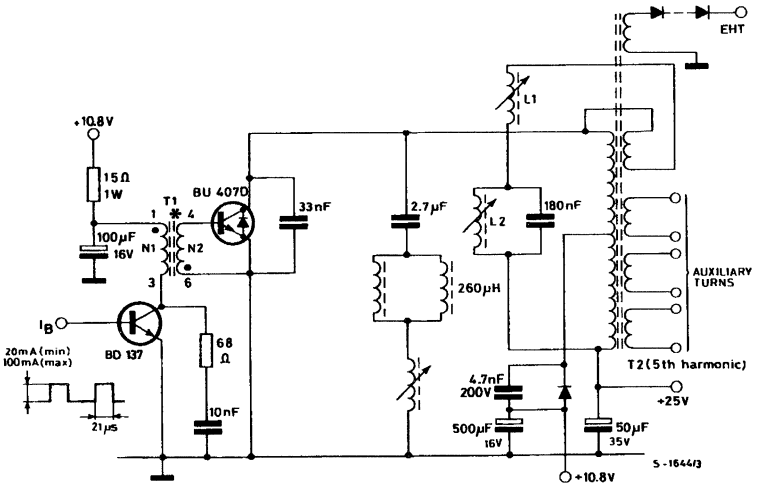
BU406D - application circuit for 17" to 24" - 110° - 28 mm neck picture tubes.



* N1 = 125 turns Ø 0.3mm ; N2 = 25 turns Ø 0.6mm ; GAP = 0.12mm ; CORE = DOUBLE E 19x5x8 mm ; FERRITE 3E1 TYPE

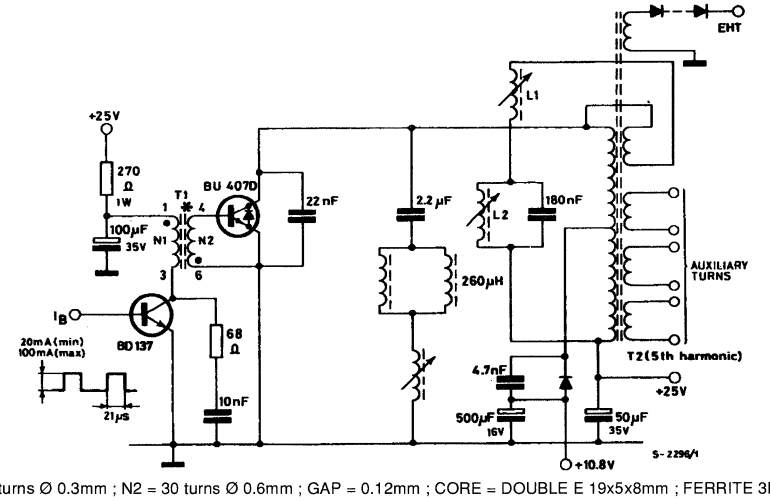
APPLICATION INFORMATION (continued)

BU407D - application circuit for 12" to 17" - 110° - 28mm neck picture tubes
(drive supply voltage = 10.8V).



* N1 = 90 turns Ø 0.3mm ; N2 = 30 turns Ø 0.6mm ; GAP = 0.12mm ; CORE = DOUBLE E 19x5x8 mm ; FERRITE 3E1 TYPE

BU407D - application circuit for 12" to 17" - 110° - 28mm neck picture tubes.
(driver supply voltage = 10.8V).



* N1 = 90 turns Ø 0.3mm ; N2 = 30 turns Ø 0.6mm ; GAP = 0.12mm ; CORE = DOUBLE E 19x5x8mm ; FERRITE 3E1 TYPE